

# Supporting Information

## Highly Sensitive Flexible Pressure Sensors Based on Printed Organic Transistors with Centro-Apically Self-Organized Organic Semiconductor Microstructures

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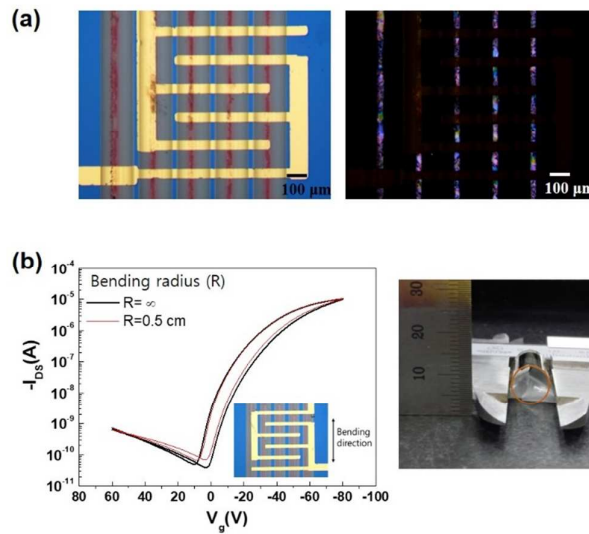
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**Figure S1.** (a) OM (left) and polarized OM (right) images of 3D OSC microstructures based on the centro-apically crystallized diF-TESADT after 80 kPa was applied to the device. (b) Comparison of transfer curves of the 3D OSC FET before and after bending of the device. (Right photograph shows bending of the device with a bending radius of 0.5 cm.)